Preface

This special edition collects recent research findings, some technological developments, and engineering practices in the field of substrate and epitaxial layer manufacturing for power electronic devices based on silicon carbide. The articles address specific aspects of epitaxial layer growth, crystal growth technologies, and substrate treatment processes, all critical to achieving the necessary structural integrity and electronic performance in advanced semiconductor devices.

The edition aims to provide a comprehensive resource for researchers, engineers, and practitioners involved in designing, developing, and manufacturing next-generation power electronic components. The articles cover both fundamental principles and applied methodologies, offering a balanced perspective on modern semiconductor technology.